

5th ISTDM

May 24-26, 2010
Stockholm, Sweden

KTH, Royal Institute of Technology



5th international SiGe Technology and Device Meeting

Organizer (KTH, Sweden) :

M. Östling: General Chair
H. H. Radamson: General Co-Chair
G. Malm, Local organizer

Abstract Submission:

The extended abstract consists of two pages including text, tables and figures.

Submission deadline:

February 12th, 2010.

Notification of acceptance:

March 12th, 2010.

Venue:

KTH, School of ICT
Kista, Stockholm

Registration & Hotel:

www.kth.se/istdm2010

Final Call for papers to ISTDM 2010

Welcome message

This meeting will provide a forum for presenting and discussing with Scope / Topics in the following technical areas:

Device-related materials

Wafer fabrication (virtual substrates, SOI, SGOI, GOI, etc.), strain adjustment and strain relaxation methods, defect engineering and characterization, layer transfer, selective growth, novel group-IV alloys and heterostructures.

Process Technology

Cleaning and treatment of SiGe(C) surfaces, epitaxy, elevated S/D contacts, SiGe gate materials, gate dielectrics on SiGe and Ge, dopant diffusion and point defects, dry etching, contact technology, process and impurity control, tooling, economics of manufacturing, process integration, local and global strain, TCAD.

Devices

Hetero-CMOS, strained MOS, HBTs, BiCMOS, MODFETs, optical devices, IR devices, tunneling, coherent and quantum devices, high-speed and THz devices, germanium devices, MEMS, thermo-electric devices, novel devices, device modeling.

Circuits / Applications

Digital logic, VLSI, MMICs, SOCs, amplifiers, mixers, wireless and fiber-optic interfaces, analog / mixed signal systems and subsystems, communications systems, components for optical communication, imaging, sensing and radar systems, emerging and novel applications.

List of invited speakers:

Philip Wong, Stanford University, USA (Keynote speaker)
Akira Toriumi, University of Tokyo, Japan
Shinchi Takagi, University of Tokyo, Japan
Shotaro Takeuchi, Nagoya University, Japan
Kohei Hamaya, Kyushu University, Japan
Tzu-Ming Lu, Princeton & NTU, USA
Kang Wang, UCLA, USA
Jingshi Hu, MIT, USA
Max Lemme, Harvard University, USA
Ya-hong Xie, UCLA, USA
Thomas Ernst, Leti, France
Benjamin Vincent, IMEC Leuven, Belgium
Zoran Ikonc, Leeds University, UK
Siegfried Mantl, FZ, Julich, Germany
Christophe Figuet, SOITEC, France
Matthias Bauer, ASM America, USA
Alexander Fox, IHP, Germany
Lis Nanver, Dimes, Delft, Netherlands
Phillip Thompson, NRL, USA
J. Andersson, Acreo, Sweden

Technical Program Chairs:

J. Murota (Tohoku Univ. Japan)
B. Tillack (IHP, Germany)
Ya-hong Xie (UCLA, USA)
H. H. Radamson (KTH, Sweden)

Other Events:

Early registration & get-together Sunday night May 23rd
Reception,
Banquet / Award Ceremony of Student & Poster Paper

Contact and information:

Abstract submission, registration and hotel booking:
ISTDM2010@congreg.com
Local organizers, technical program, etc :
istdm2010@ict.kth.se

Advisory committee:

M. Caymax (IMEC, Belgium)
S.-J. Chang (National Cheng Kung Univ., Taiwan)
J. Derrien (Univ. Mediterranean, France)
E. A. Fitzgerald (MIT, USA)
D. Grützmacher (FZ-Juelich, Germany)
J.-M. Hartmann (CEA/Leti, France)
J. L. Hoyt (MIT, USA)
E. Kasper (Stuttgart Univ., Germany)
T.-J. King (UC Berkeley, USA)
S. J. Koester (IBM, USA)
J. Murota (Tohoku Univ., Japan)
W.-X. Ni (LiTH, Sweden)
Y. Shiraki (Tokyo City Univ., Japan)
J. C. Sturm (Princeton Univ., USA)
B. Tillack (IHP, Germany)
Y. Yasuda (Tohoku Univ., Japan)
S. Zaima (Nagoya Univ., Japan)
M. Östling (KTH, Sweden)
Ya-Hong Xie (UCLA, USA)

Publications:

Authors of accepted abstracts are encouraged to submit a full paper for publication in a special issue of Solid State Electronics. Selected papers will be included in the special issue, after a full review process.

Manuscripts are due May 26th, 2010, and should be emailed to the conference organizers at: istdm2010@ict.kth.se

Manuscripts should have a length of 6 to 10 journal pages and must describe original, substantial work of high quality, suitable for the journal. Please note that papers that are clearly too short or too long will be rejected without review.

